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### RF TRANSISTORS

2N3932 2N3933

2N3932 and 2N3933 are epitaxial planar transistors of the silicon npn type, with characteristics which make them extremely useful as general-purpose rf amplifiers at frequencies up to 450 MHz.

These characteristics include low noise figures at 60, 200, and 450 MHz low feedback capacitance, high gain-bandwidth product, and high power gains in unneutralized amplifier circuits.

The 2N3932 and 2N3933 utilize a compact, hermetically sealed four-lead metal package, in which the active elements of the transistor are insulated from the case. The construction of these devices contributes to highly reliable performance at very- and ultra-high-frequencies, and permits grounding of the case to minimize feedback capacitances and undesired coupling —a feature not available in devices using conventional epoxy-type enclosures.

### Maximum Ratings, Absolute-Maximum Values:

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•	2N3932	2N393	13
Collector-to-Base Voltage,	30	40 max.	<b>v</b>
Collector-to-Emitter Voltage,	20	30 max.	v
Emitter-to-Base Voltage, VEBO · · · · · · · · · · · · · · · · · · ·	2.5	2,5 max.	v
Collector Current, IC	limi	ted by dissip	pation
Transistor Dissipation, PT:			
at ambient   up to 25° C temperatures   above 25° C	200	200 max.	m₩ Fig. 1
Temperature Range:			
Storage and Operating (Junction)	-6	5 to 200° C	
Lead Temperature (During Soldering): At distances not less than 1/16" from seat- ing surface for 10			
seconds	265	265 max.	۰c

## SILICON NPN EPITAXIAL PLANAR TYPES



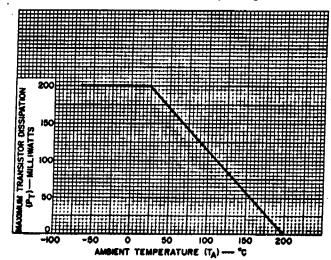
# For VHF and UHF Applications in Industrial and Military Equipment

#### **FEATURES**

low noise figures (NF):

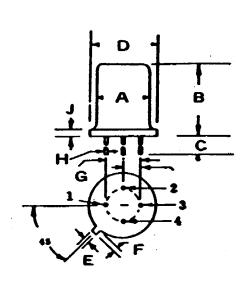
2N3932	2N3933	
2.5 dB typ.	3 dB max.	@ 60 MHz
4.5 dB max.	4 dB max.	@ 200 MHz
5 dB typ.	5 dB typ.	@ 450 MHz

- high gain-bandwidth product (f<sub>T</sub>):
   750 MHz min. for both types
- e-low collector-to-base time constant ( $r_b$ '  $C_c$ ): 2N3932 = 8 ps max. 2N3933 = 6 ps max.
- high unneutralized power gain (Gpe);
   2N3932 = 11.5dB min. at 200 MHz
   2N3933 = 14 dB min. at 200 MHz
- low output capacitance (C<sub>cb</sub>):
   C<sub>cb</sub> = 0.55 pF max. for both types
- e hermetically sealed metal 4-lead package





NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.



	•								
	A	В	C	Ď	Ē	F	G	H	J
R176	.195	.210	.500	.230	,036	.036	_100	,016	.030
			MIN		,046	,048	i :	.019	1
R176a	.195	.346	.500	.230	.036	,036	.100	.016	.030
			MIN		,046	,048		019	
R176b	.220	.170	.500		.036	028	.100	.016	.030
٠.	.240	.210	MIN	1	.046	.048	1	.019	MAX
R176c	.305	.150	.500	,335	.028	.029	. 200	-016	.009
	.335	.260	MIN	.370	.034	.045	BSC	.021	. 125
R176d	.324	.259	.748	.370	.031	.029	. 200	.017	.027
		MAX		MAX	1		1		
R176e	.315	.240	.500	340	.028	029		.016	
	.335	.260	MIN	.370	.034	.043		.021	
R176f	.194	.208	.539	. 228	1		.098	.018	
		1	<u> </u>				1	MAX	
R176g	.192	.208	.118	.229			.106	.019	
	MAX	<u> </u>	<u>L.                                    </u>			<b>!</b>	<u></u>	MAX	
R176h	.335	.260	.748	.370	.031	.031	. 200	.016	.039
	MAX	MAX	MIN	MAX				MIN	
R176J	.334	.259	.925	.369	.031	.031	_ 200	.016	.039
	MAX	MAX	MIN	MAX		<u> </u>		<u> </u>	<b>!</b>
R176k		.210	.500	.230	1	l	l	İ	
	<u> </u>	<u> </u>	MIN	<u> </u>	<u></u>	<u> </u>	<u> </u>	<u></u>	<u> </u>